

# NVMFS5C410NL

## Power MOSFET

40 V, 0.82 mΩ, 330 A, Single N-Channel

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- NVMFS5C410NLWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			$V_{DSS}$	40	V	
Gate-to-Source Voltage			$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^{\circ}\text{C}$	$I_D$	330	A	
		$T_C = 100^{\circ}\text{C}$		230		
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	$P_D$	167	W	
		$T_C = 100^{\circ}\text{C}$		83		
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^{\circ}\text{C}$	$I_D$	50	A	
		$T_A = 100^{\circ}\text{C}$		35		
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)		$T_A = 25^{\circ}\text{C}$	$P_D$	3.8	W	
		$T_A = 100^{\circ}\text{C}$		1.9		
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$ , $t_p = 10\text{ }\mu\text{s}$		$I_{DM}$	900	A	
Operating Junction and Storage Temperature			$T_J$ , $T_{stg}$	-55 to +175	$^{\circ}\text{C}$	
Source Current (Body Diode)			$I_S$	169	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 29\text{ A}$ )			$E_{AS}$	706	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			$T_L$	260	$^{\circ}\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

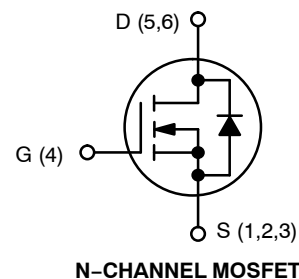
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



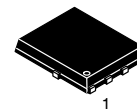
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	0.82 mΩ @ 10 V	330 A
	1.2 mΩ @ 4.5 V	

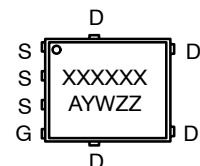


N-CHANNEL MOSFET



DFN5  
(SO-8FL)  
CASE 488AA  
STYLE 1

### MARKING DIAGRAM



XXXXXX = 5C410L  
(NVMFS5C410NL) or  
410LWF  
(NVMFS5C410NLWF)

A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVMFS5C410NL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			21.2		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 40 V	T <sub>J</sub> = 25 °C		10	μA
			T <sub>J</sub> = 125°C		250	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA

### ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.2		2.0	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			-5.75		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 50 A	0.65	0.82	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 50 A	0.95	1.2	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 50 A		190		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V		8862		pF
Output Capacitance	C <sub>OSS</sub>			4156		
Reverse Transfer Capacitance	C <sub>RSS</sub>			116		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		66		nC
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		143		
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		6.75		
Gate-to-Source Charge	Q <sub>GS</sub>			21.4		
Gate-to-Drain Charge	Q <sub>GD</sub>			22		
Plateau Voltage	V <sub>GP</sub>			2.7		V

### SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V, I <sub>D</sub> = 50 A, R <sub>G</sub> = 1.0 Ω		20		ns
Rise Time	t <sub>r</sub>			130		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			66		
Fall Time	t <sub>f</sub>			177		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 50 A	T <sub>J</sub> = 25°C		0.73	1.2	V
			T <sub>J</sub> = 125°C		0.6		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 50 A		79.5		ns	
Charge Time	t <sub>a</sub>			39			
Discharge Time	t <sub>b</sub>			40.5			
Reverse Recovery Charge	Q <sub>RR</sub>			126		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

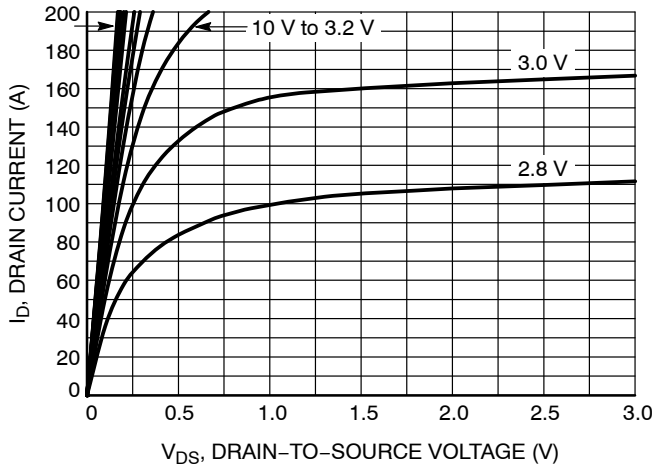


Figure 1. On-Region Characteristics

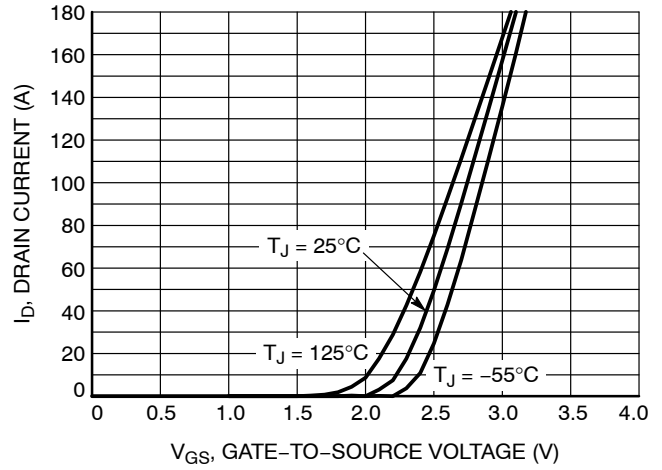


Figure 2. Transfer Characteristics

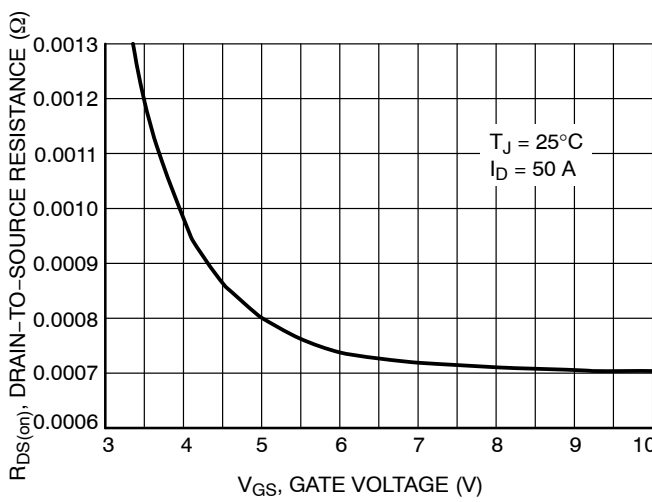


Figure 3. On-Resistance vs. Gate-to-Source Voltage

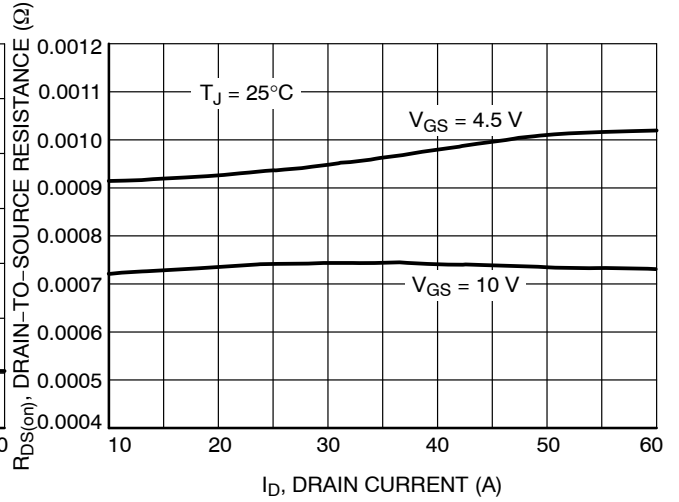


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

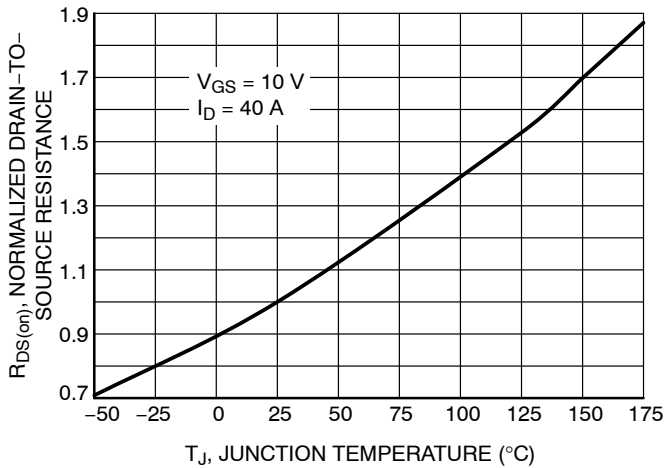


Figure 5. On-Resistance Variation with Temperature

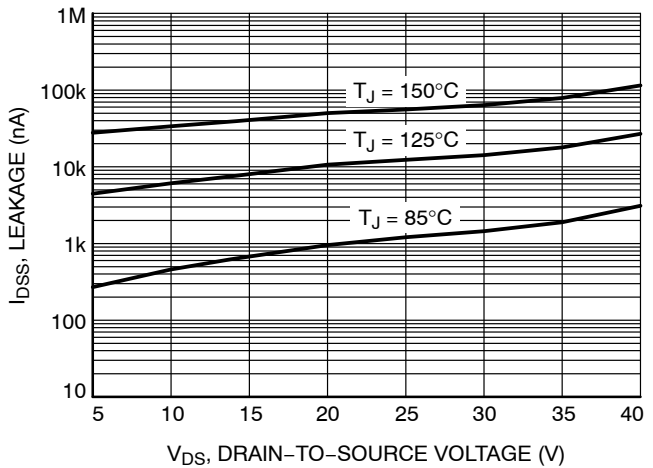


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

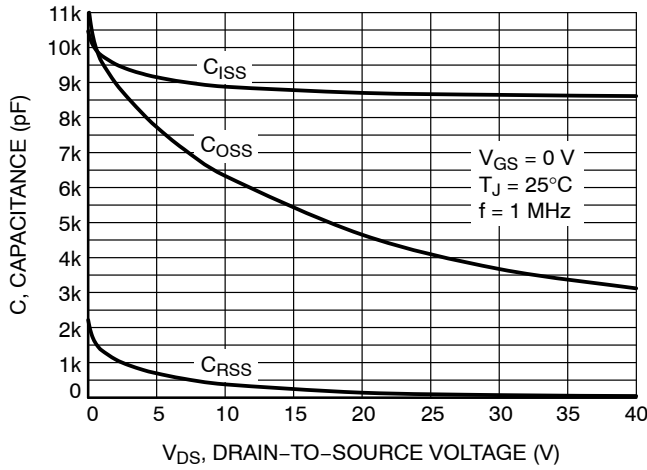


Figure 7. Capacitance Variation

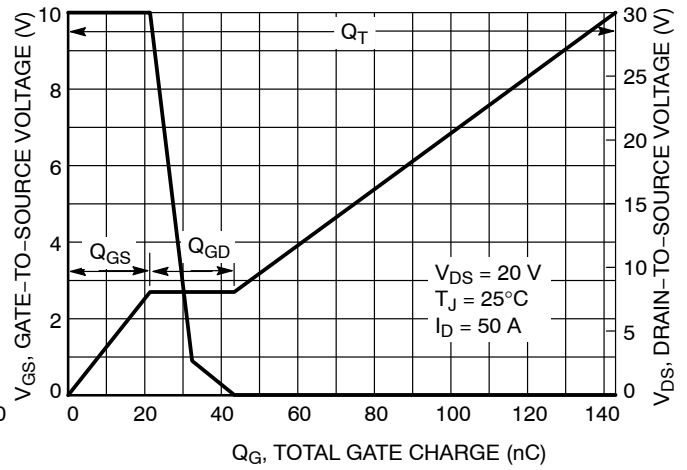


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

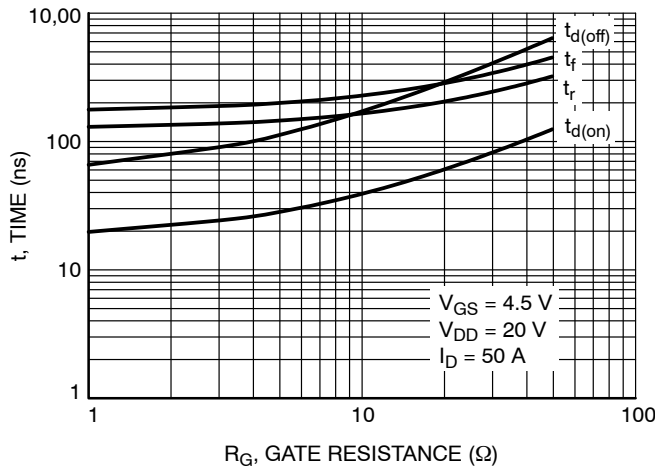


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

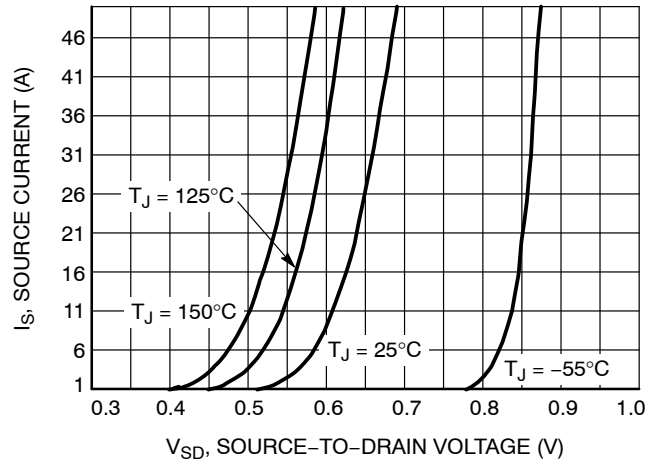


Figure 10. Diode Forward Voltage vs. Current

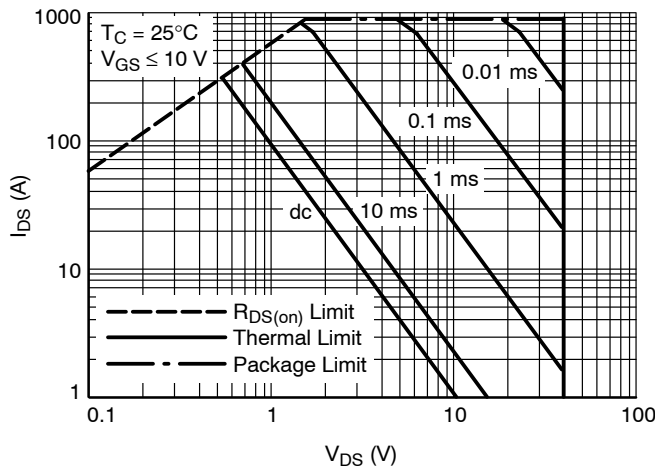


Figure 11. Safe Operating Area

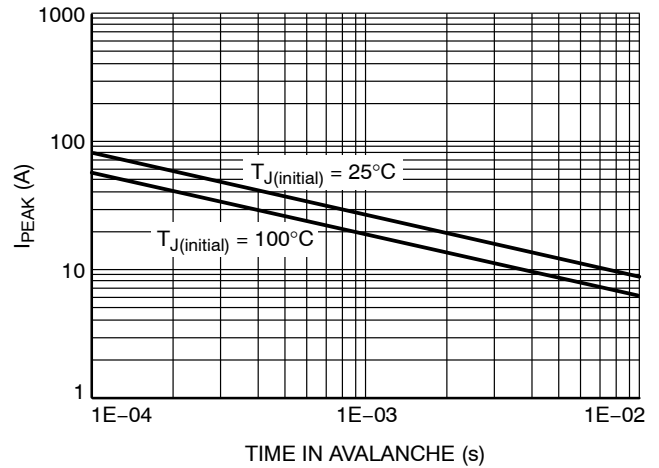
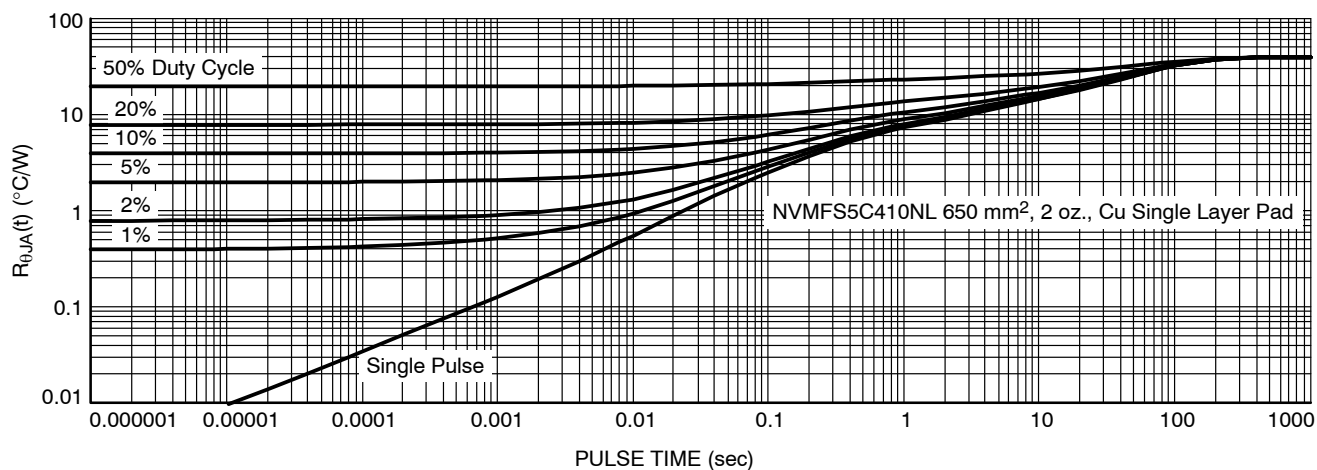


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

## NVMFS5C410NL



**Figure 13. Thermal Characteristics**

### DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NVMFS5C410NLT1G	5C410L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C410NLWFT1G	410LWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS5C410NLT3G	5C410L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C410NLWFT3G	410LWF	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel
NVMFS5C410NLAFT1G	5C410L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C410NLWFAFT1G	410LWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVMFS5C410NL

## PACKAGE DIMENSIONS

DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE M

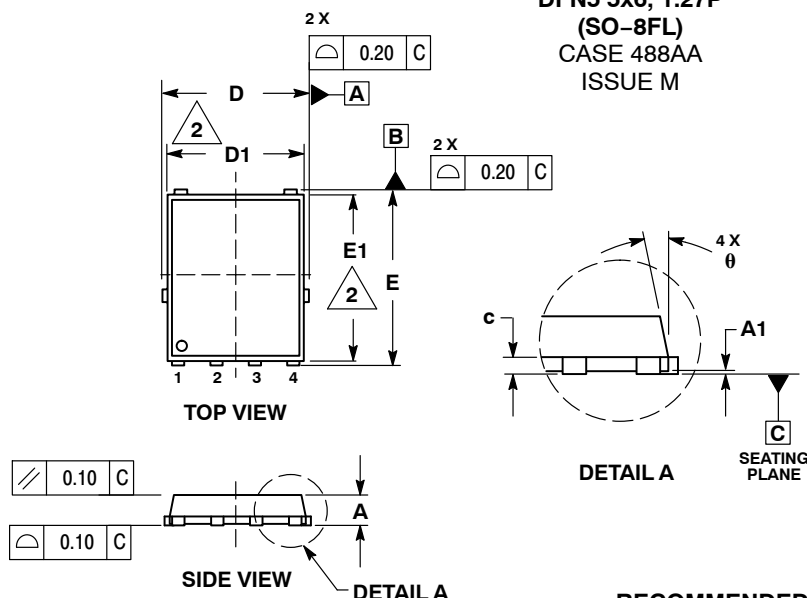
### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

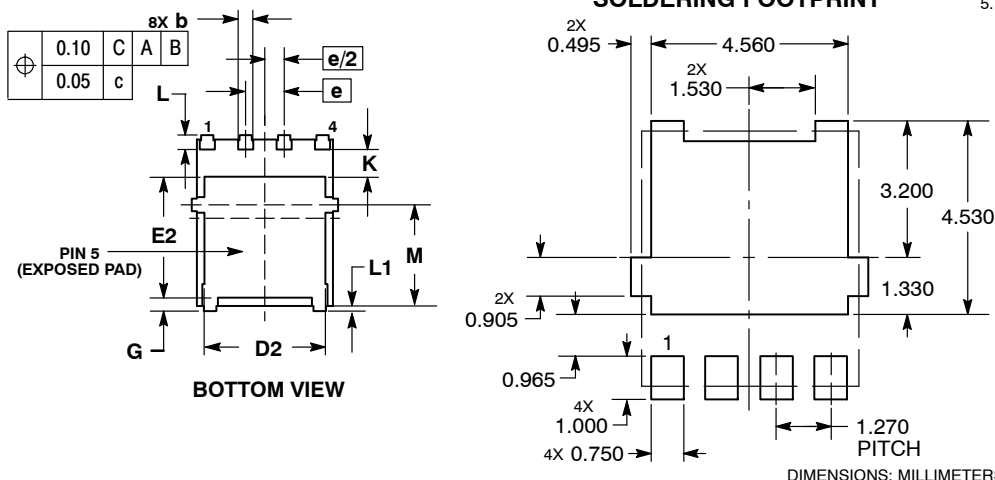
MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

### STYLE 1:


- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN



### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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